



Description

The HXY60N02D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 20V$ $I_D = 60A$

$R_{DS(ON)} < 6m\Omega$ @ $V_{GS}=4.5V$

Application

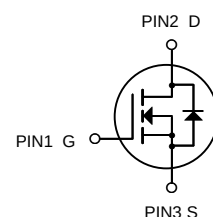
Battery protection

Load switch

Uninterruptible power supply



TO-252-2L



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY60N02D	TO-252-2L	60N02D XXX YYYY	2500

Absolute Maximum Ratings ($T_c=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	60	A
$I_D(100^{\circ}C)$	Drain Current-Continuous($T_c=100^{\circ}C$)	42	A
I_{DM}	Pulsed Drain Current	210	A
P_D	Maximum Power Dissipation	60	W
	Derating factor	0.48	W/ $^{\circ}C$
E_{AS}	Single pulse avalanche energy (Note 5)	200	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 2)	2.1	$^{\circ}C/W$



Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.75	1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=20A$	-	4.5	6	m Ω
		$V_{GS}=2.5V, I_D=15A$		5.3	8.2	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=20A$	15	-	-	S
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	2000	-	PF
Output Capacitance	C_{oss}		-	500	-	PF
Reverse Transfer Capacitance	C_{rss}		-	200	-	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=2A, R_L=1\Omega$ $V_{GS}=4.5V, R_G=3\Omega$	-	6.4	-	nS
Turn-on Rise Time	t_r		-	17.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29.6	-	nS
Turn-Off Fall Time	t_f		-	16.8	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=20A,$ $V_{GS}=10V$	-	27		nC
Gate-Source Charge	Q_{gs}		-	6.5		nC
Gate-Drain Charge	Q_{gd}		-	6.4		nC
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=10A$	-		1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	60	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}, I_F = 20A$ $di/dt = 100A/\mu s^{(Note3)}$	-	25	-	nS
Reverse Recovery Charge	Q_{rr}		-	24	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : $T_J=25^{\circ}\text{C}, V_{DD}=10V, V_G=10V, L=0.5mH, R_g=25\Omega,$



Typical Electrical and Thermal Characteristics (Curves)

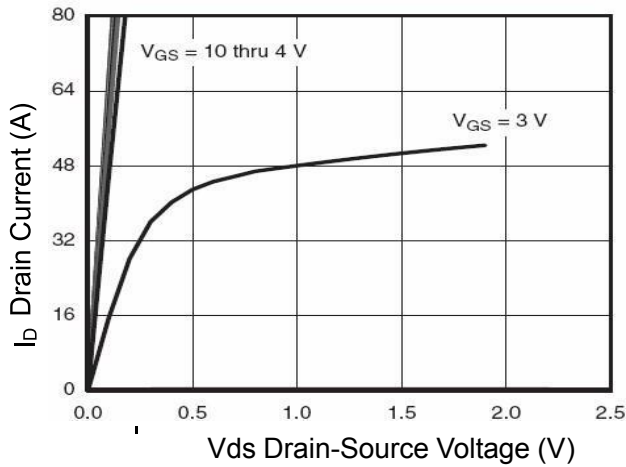


Figure 1 Output Characteristics

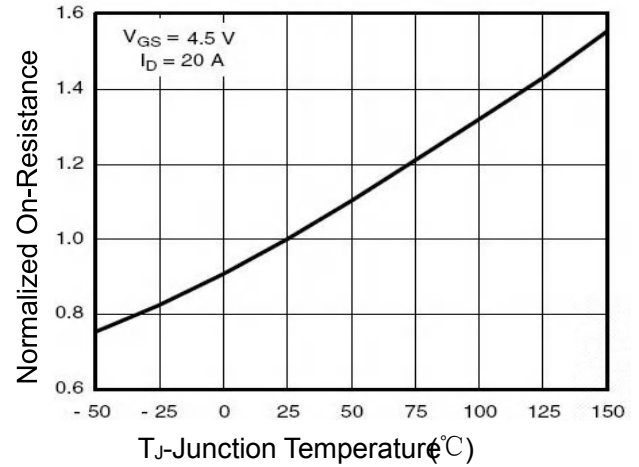


Figure 4 $R_{DS(on)}$ -Junction Temperature

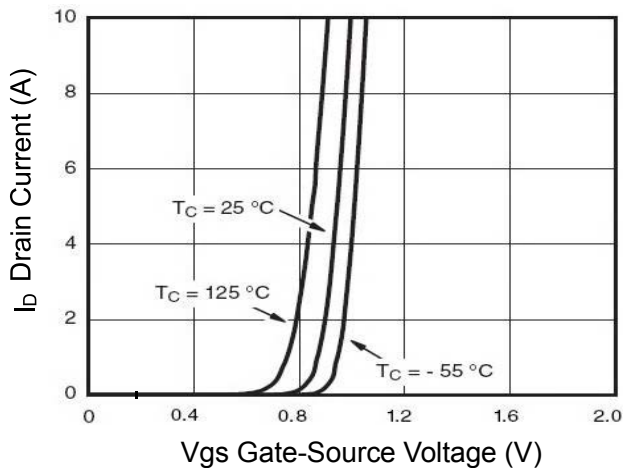


Figure 2 Transfer Characteristics

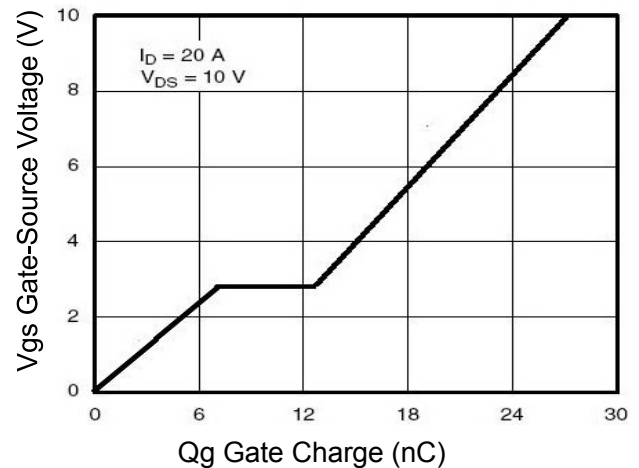


Figure 5 Gate Charge

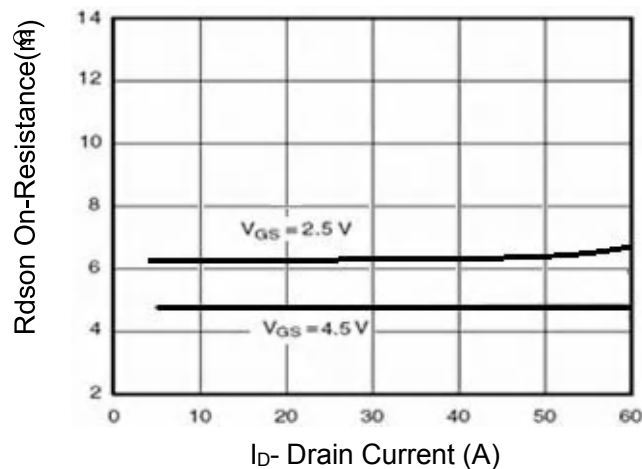


Figure 3 $R_{DS(on)}$ - Drain Current

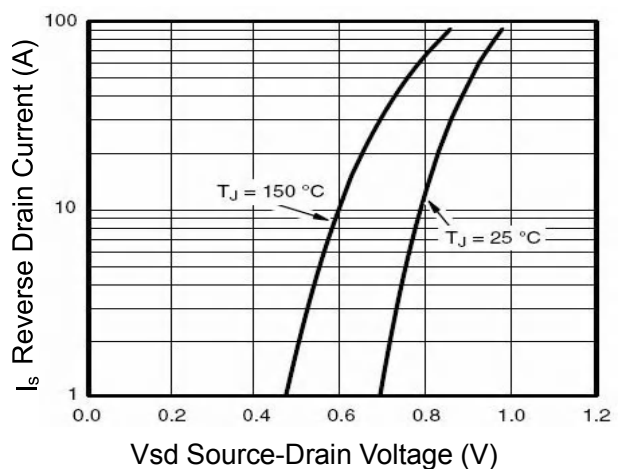
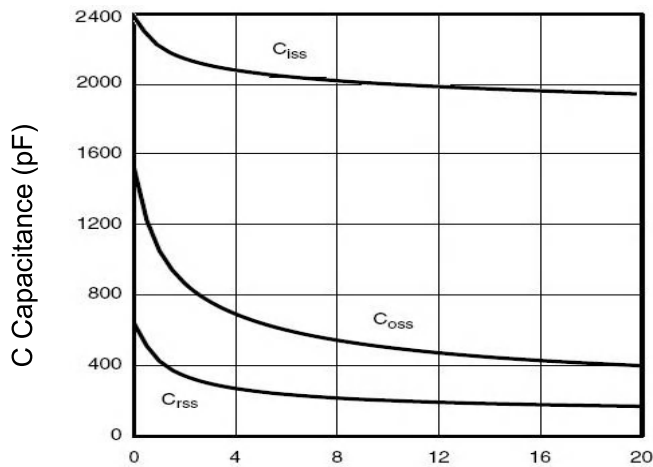
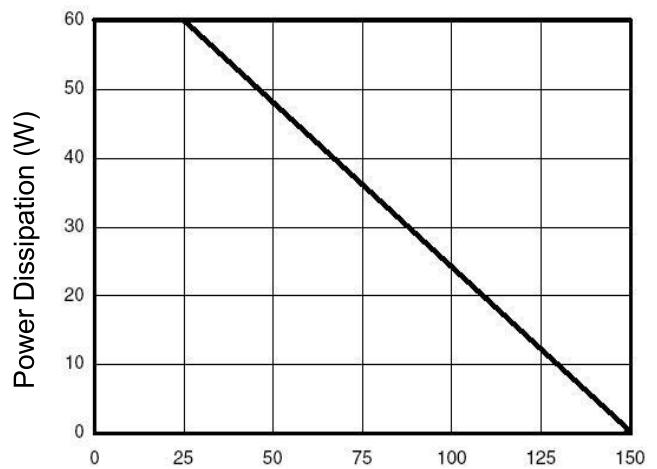


Figure 6 Source- Drain Diode Forward



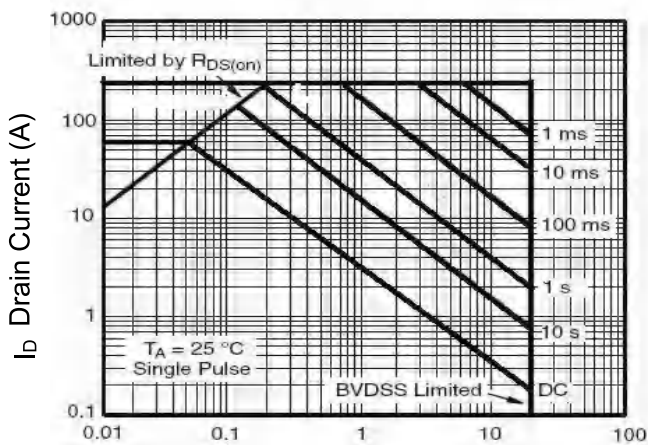
Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



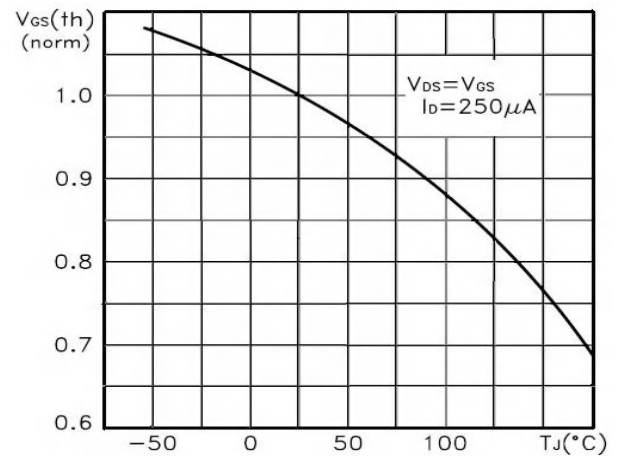
TJ-Junction Temperature (°C)

Figure 9 Power De-rating



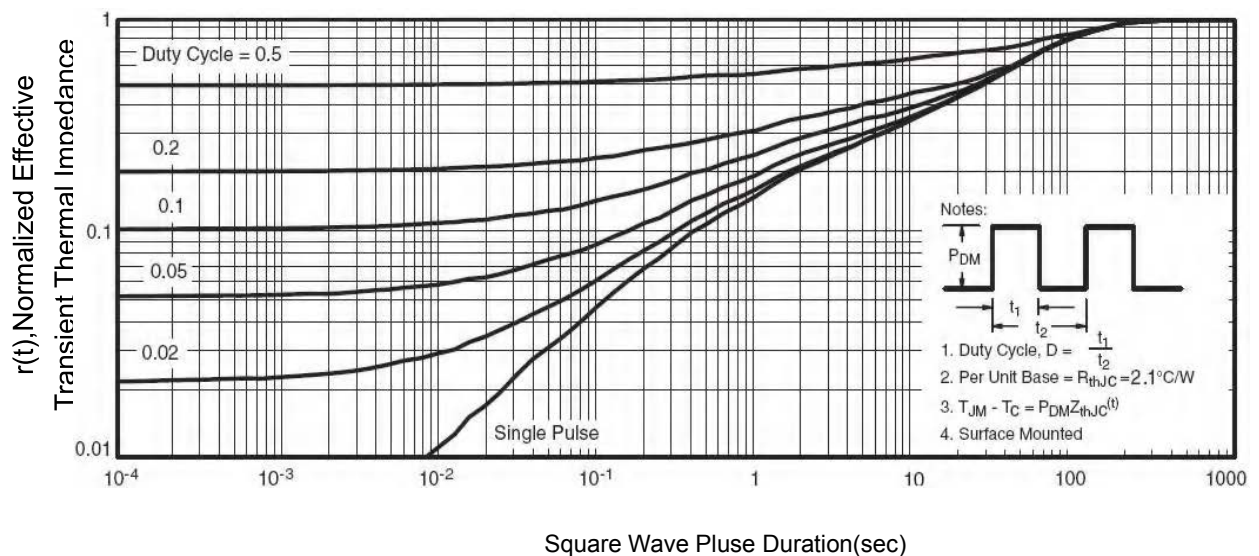
Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area



TJ-Junction Temperature(°C)

Figure 10 VGS(th) vs Junction Temperature



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



N-Channel Enhancement Mode MOSFET

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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